



PATENT
Atty. Dkt. No. AMAT/2966P2/DD/BCVD/JW

2823

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Huang

Serial No.: 09/270,039

Confirmation No.: 0424

Filed: March 16, 1999

For: **IN SITU DEPOSITION OF A
LOW K DIELECTRIC LAYER,
BARRIER LAYER, ETCH
STOP, AND ANTI-
REFLECTIVE COATING FOR
DAMASCENE APPLICATION**

Group Art Unit: 2823

Examiner: G. FOURSON

TECHNOLOGY CENTER 280

1. The first step is to identify the problem or question that needs to be answered. This involves understanding the context and the specific requirements of the task.

RECEIVED

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

CERTIFICATE OF MAILING
37 CFR 1.8

I hereby certify that this correspondence is being deposited on 5/24, 2001 with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

5/24/01
Date

Kent E. Fisher
Signature

RESPONSE TO RESTRICTION REQUIREMENT DATED APRIL 24, 2001

In response to the Office Action dated April 24, 2001, having a shortened statutory period for response set to expire on May 24, 2001, the Applicants elect claims 14-29. Please enter the following amendments and reconsider the restriction pending in the application for reasons discussed below.

IN THE CLAIMS:

Please cancel claim 5, and amend the claims as follows:

1. (Amended) A substrate, comprising:
a silicon carbide layer having a dielectric constant less than 7.0 and deposited on the substrate;
a first dielectric layer deposited on the silicon carbide layer *in situ* with the silicon carbide layer; and
a photoresist layer deposited on the first dielectric layer.